# RF Power LDMOS Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

This 55 W asymmetrical Doherty RF power LDMOS transistor is designed for cellular base station applications requiring very wide instantaneous bandwidth capability covering the frequency range of 1880 to 2025 MHz.

**1880–2025 MHz**

- Typical Doherty single-carrier W-CDMA performance: $V_{DD}$ = 28 Vdc, $I_{DQA}$ = 700 mA, $V_{GSB}$ = 0.1 Vdc, $P_{out}$ = 55 W Avg., input signal PAR = 9.9 dB @ 0.01% probability on CCDF.

| Frequency | $G_{ps}$ (dB) | $\eta_D$ (%) | Output PAR (dB) | ACPR (dBc) |
|---|---|---|---|---|
| 1880 MHz | 15.6 | 49.6 | 7.8 | –31.2 |
| 1960 MHz | 16.3 | 50.3 | 7.8 | –32.1 |
| 2025 MHz | 15.3 | 47.4 | 7.6 | –33.1 |

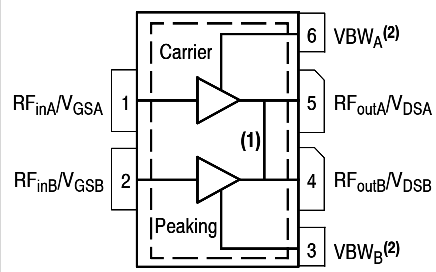
### Features

- Advanced high performance in-package Doherty
- Designed for wide instantaneous bandwidth applications
- Greater negative gate-source voltage range for improved Class C operation
- Designed for digital predistortion error correction systems

**A2T20H330W24NR6**

**1880–2025 MHz, 55 W AVG., 28 V AIRFAST RF POWER LDMOS TRANSISTOR**

**OM-1230-4L2L PLASTIC**




(Top View)

Note: Exposed backside of the package is the source terminal for the transistor.

**Figure 1. Pin Connections**

1. Pin connections 4 and 5 are DC coupled and RF independent.
2. Device cannot operate with $V_{DD}$ current supplied through pin 3 and pin 6.

## Table 1. Maximum Ratings

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DSS}$ | –0.5, +65 | Vdc |
| Gate-Source Voltage | $V_{GS}$ | –6.0, +10 | Vdc |
| Operating Voltage | $V_{DD}$ | 32, +0 | Vdc |
| Storage Temperature Range | $T_{stg}$ | –65 to +150 | °C |
| Case Operating Temperature Range | $T_C$ | –40 to +125 | °C |
| Operating Junction Temperature Range [1,2] | $T_J$ | –40 to +225 | °C |

## Table 2. Thermal Characteristics

| Characteristic | Symbol | Value [2,3] | Unit |
|---|---|---|---|
| Thermal Resistance, Junction to Case<br>Case Temperature 76°C, 55 W Avg., W-CDMA, 28 Vdc, $I_{DQA}$ = 700 mA,<br>$V_{GSB}$ = 0.1 Vdc, f = 1960 MHz | $R_{\theta JC}$ | 0.26 | °C/W |

## Table 3. ESD Protection Characteristics

| Test Methodology | Class |
|---|---|
| Human Body Model (per JESD22-A114) | 2 |
| Machine Model (per EIA/JESD22-A115) | B |
| Charge Device Model (per JESD22-C101) | IV |

## Table 4. Moisture Sensitivity Level

| Test Methodology | Rating | Package Peak Temperature | Unit |
|---|---|---|---|
| Per JESD22-A113, IPC/JEDEC J-STD-020 | 3 | 260 | °C |

## Table 5. Electrical Characteristics ($T_A$ = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| **Off Characteristics** [4] | | | | | |
| Zero Gate Voltage Drain Leakage Current<br>($V_{DS}$ = 65 Vdc, $V_{GS}$ = 0 Vdc) | $I_{DSS}$ | — | — | 10 | μAdc |
| Zero Gate Voltage Drain Leakage Current<br>($V_{DS}$ = 32 Vdc, $V_{GS}$ = 0 Vdc) | $I_{DSS}$ | — | — | 5 | μAdc |
| Gate-Source Leakage Current<br>($V_{GS}$ = 5 Vdc, $V_{DS}$ = 0 Vdc) | $I_{GSS}$ | — | — | 1 | μAdc |
| **On Characteristics - Side A, Carrier** | | | | | |
| Gate Threshold Voltage<br>($V_{DS}$ = 10 Vdc, $I_D$ = 140 μAdc) | $V_{GS(th)}$ | 0.8 | 1.2 | 2.2 | Vdc |
| Gate Quiescent Voltage<br>($V_{DD}$ = 28 Vdc, $I_D$ = 700 mAdc, Measured in Functional Test) | $V_{GSA(Q)}$ | 2.3 | 2.6 | 3.1 | Vdc |
| Drain-Source On-Voltage<br>($V_{GS}$ = 10 Vdc, $I_D$ = 1.4 Adc) | $V_{DS(on)}$ | 0.1 | 0.15 | 0.3 | Vdc |
| **On Characteristics - Side B, Peaking** | | | | | |
| Gate Threshold Voltage<br>($V_{DS}$ = 10 Vdc, $I_D$ = 180 μAdc) | $V_{GS(th)}$ | 0.8 | 1.2 | 1.6 | Vdc |
| Drain-Source On-Voltage<br>($V_{GS}$ = 10 Vdc, $I_D$ = 1.8 Adc) | $V_{DS(on)}$ | 0.1 | 0.15 | 0.3 | Vdc |

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at http://www.nxp.com/RF/calculators.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.nxp.com/RF and search for AN1955.
4. Side A and Side B are tied together for these measurements.

(continued)

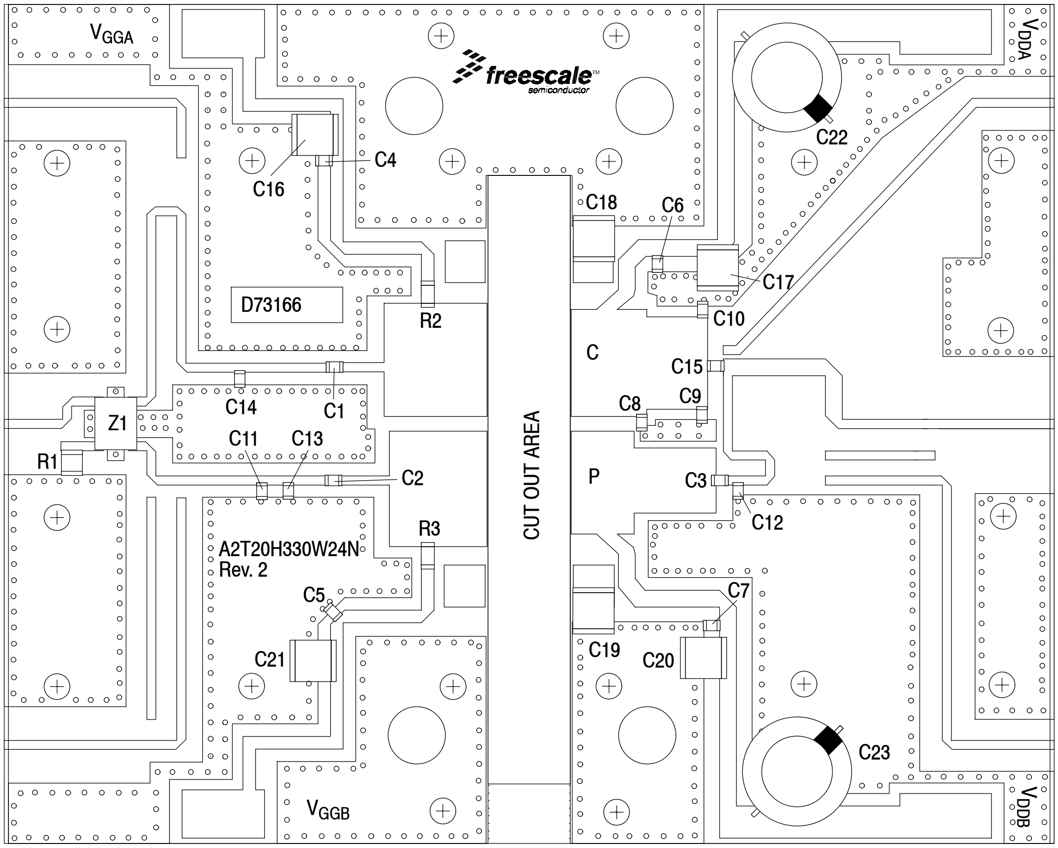
**Table 5. Electrical Characteristics** ($T_A$ = 25°C unless otherwise noted) **(continued)**

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| **Functional Tests** [1,2,3] (In NXP Doherty Test Fixture, 50 ohm system) $V_{DD}$ = 28 Vdc, $I_{DQA}$ = 700 mA, $V_{GSB}$ = 0.1 Vdc, $P_{out}$ = 55 W Avg., f = 1880 MHz, Single‑Carrier W‑CDMA, IQ Magnitude Clipping, Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. | | | | | |
| Power Gain | $G_{ps}$ | 14.8 | 15.9 | 17.8 | dB |
| Drain Efficiency | $\eta_D$ | 46.7 | 49.8 | — | % |
| Output Peak‑to‑Average Ratio @ 0.01% Probability on CCDF | PAR | 7.4 | 7.9 | — | dB |
| Adjacent Channel Power Ratio | ACPR | — | –32.8 | –28.7 | dBc |
| **Load Mismatch** [3] (In NXP Doherty Test Fixture, 50 ohm system) $I_{DQA}$ = 700 mA, $V_{GSB}$ = 0.1 Vdc, f = 1960 MHz, 12 μsec(on), 10% Duty Cycle | | | | | |
| VSWR 5:1 at 28 Vdc, 191 W Pulsed CW Output Power (0 dB Input Overdrive from 191 W Pulsed CW Rated Power) | No Device Degradation | | | | |
| **Typical Performance** [3] (In NXP Doherty Test Fixture, 50 ohm system) $V_{DD}$ = 28 Vdc, $I_{DQA}$ = 700 mA, $V_{GSB}$ = 0.1 Vdc, 1880–2025 MHz Bandwidth | | | | | |
| $P_{out}$ @ 1 dB Compression Point, CW | P1dB | — | 229 | — | W |
| $P_{out}$ @ 3 dB Compression Point [4] | P3dB | — | 383 | — | W |
| AM/PM (Maximum value measured at the P3dB compression point across the 1880–2025 MHz bandwidth) | Φ | — | –13 | — | ° |
| VBW Resonance Point (IMD Third Order Intermodulation Inflection Point) | $VBW_{res}$ | — | 130 | — | MHz |
| Gain Flatness in 145 MHz Bandwidth @ $P_{out}$ = 55 W Avg. | $G_F$ | — | 0.8 | — | dB |
| Gain Variation over Temperature (–30°C to +85°C) | ΔG | — | 0.001 | — | dB/°C |
| Output Power Variation over Temperature (–30°C to +85°C) | ΔP1dB | — | 0.003 | — | dB/°C |

**Table 6. Ordering Information**

| Device | Tape and Reel Information | Package |
|---|---|---|
| A2T20H330W24NR6 | R6 Suffix = 150 Units, 56 mm Tape Width, 13‑inch Reel | OM‑1230‑4L2L |

1. $V_{DDA}$ and $V_{DDB}$ must be tied together and powered by a single DC power supply.
2. Part internally matched both on input and output.
3. Measurements made with device in an asymmetrical Doherty configuration.
4. P3dB = $P_{avg}$ + 7.0 dB where $P_{avg}$ is the average output power measured using an unclipped W‑CDMA single‑carrier input signal where output PAR is compressed to 7.0 dB @ 0.01% probability on CCDF.




Note: $V_{DDA}$ and $V_{DDB}$ must be tied together and powered by a single DC power supply.

**Figure 2. A2T20H330W24NR6 Test Circuit Component Layout**

**Table 7. A2T20H330W24NR6 Test Circuit Component Designations and Values**

| Part | Description | Part Number | Manufacturer |
|---|---|---|---|
| C1, C2, C3, C4, C5, C6, C7 | 8.2 pF Chip Capacitors | ATC600F8R2JT250XT | ATC |
| C8, C9, C10, C11 | 0.3 pF Chip Capacitors | ATC600F0R3JT250XT | ATC |
| C12 | 0.5 pF Chip Capacitor | ATC600F0R5BT250XT | ATC |
| C13 | 0.6 pF Chip Capacitor | ATC600F0R6BT250XT | ATC |
| C14 | 1.1 pF Chip Capacitor | ATC600F1R1BT250XT | ATC |
| C15 | 7.5 pF Chip Capacitor | ATC600F7R5BT250XT | ATC |
| C16, C17, C18, C19, C20, C21 | 10 μF Chip Capacitors | C5750X7S2A106M230KB | TDK |
| C22, C23 | 220 μF, 50 V Electrolytic Capacitors | 227CKS050M | Illinois Capacitor |
| R1 | 50 Ω, 10 W Chip Resistor | C10A50Z4 | Anaren |
| R2, R3 | 2.7 Ω, 1/4 W Chip Resistors | CRCW12062R70FKEA | Vishay |
| Z1 | 1800–2200 MHz Band, 90°, 5 dB Directional Coupler | X3C19P1-05S | Anaren |
| PCB | Rogers RO4350B, 0.020″, $\varepsilon_r$ = 3.66 | D73166 | MTL |

## TYPICAL CHARACTERISTICS — 1880–2025 MHz

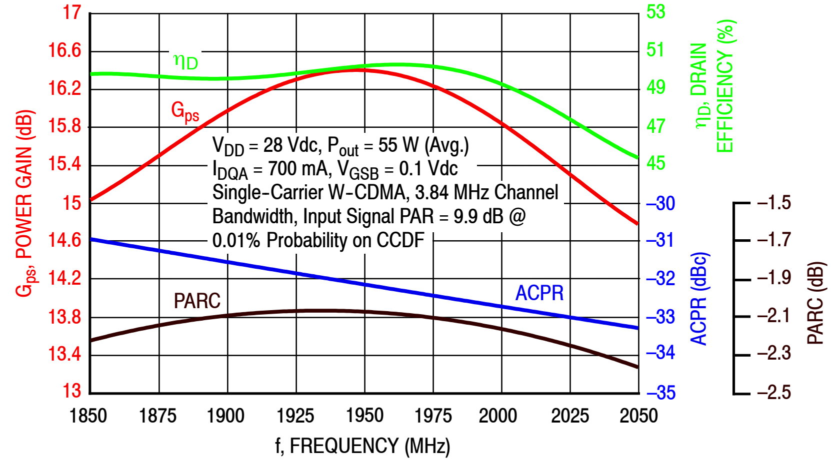



**Figure 3. Single-Carrier Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @ $P_{out}$ = 55 Watts Avg.**

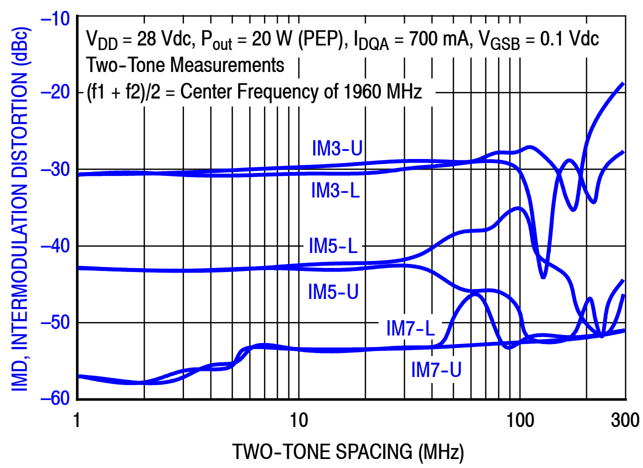



**Figure 4. Intermodulation Distortion Products versus Two-Tone Spacing**

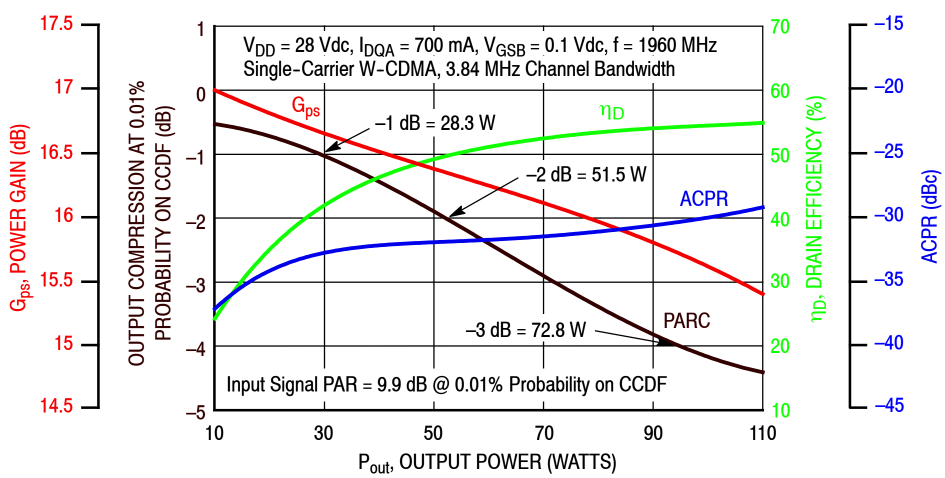



**Figure 5. Output Peak-to-Average Ratio Compression (PARC) versus Output Power**

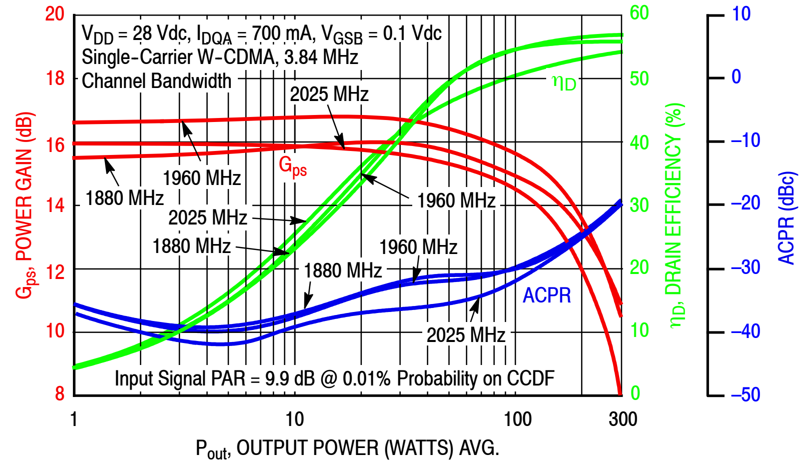



**Figure 6. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power**

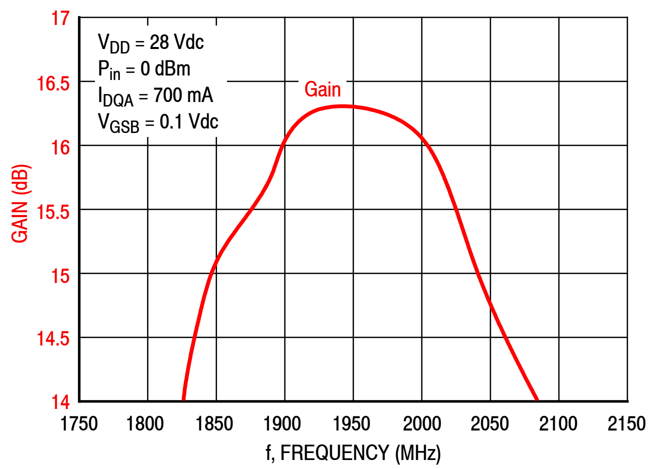



**Figure 7. Broadband Frequency Response**

**Table 8. Carrier Side Load Pull Performance — Maximum Power Tuning**

$V_{DD}$ = 28 Vdc, $I_{DQA}$ = 697 mA, Pulsed CW, 10 μsec(on), 10% Duty Cycle

| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | Max Output Power | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P1dB | | | | | |
| | | | $Z_{load}$ (1) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 0.90 – j3.49 | 1.03 + j3.46 | 1.10 – j2.83 | 19.6 | 51.9 | 155 | 56.9 | –15 |
| 1960 | 2.03 – j4.74 | 1.94 + j4.58 | 1.13 – j2.91 | 19.5 | 51.9 | 156 | 56.8 | –15 |
| 2025 | 4.03 – j6.34 | 4.09 + j5.83 | 1.14 – j2.94 | 19.5 | 51.8 | 152 | 55.2 | –15 |

| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | Max Output Power | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P3dB | | | | | |
| | | | $Z_{load}$ (2) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 0.90 – j3.49 | 0.95 + j3.53 | 1.06 – j2.94 | 17.3 | 52.7 | 186 | 58.1 | –19 |
| 1960 | 2.03 – j4.74 | 1.85 + j4.74 | 1.13 – j3.04 | 17.2 | 52.7 | 185 | 58.1 | –18 |
| 2025 | 4.03 – j6.34 | 4.10 + j6.23 | 1.15 – j3.06 | 17.2 | 52.6 | 181 | 56.7 | –19 |

(1) Load impedance for optimum P1dB power.
(2) Load impedance for optimum P3dB power.
$Z_{source}$ = Measured impedance presented to the input of the device at the package reference plane.
$Z_{in}$ = Impedance as measured from gate contact to ground.
$Z_{load}$ = Measured impedance presented to the output of the device at the package reference plane.

**Table 9. Carrier Side Load Pull Performance — Maximum Efficiency Tuning**

$V_{DD}$ = 28 Vdc, $I_{DQA}$ = 697 mA, Pulsed CW, 10 μsec(on), 10% Duty Cycle

| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | Max Drain Efficiency | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P1dB | | | | | |
| | | | $Z_{load}$ (1) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 0.90 – j3.49 | 1.15 + j3.85 | 3.07 – j1.83 | 23.0 | 49.0 | 79 | 68.3 | –17 |
| 1960 | 2.03 – j4.74 | 2.50 + j4.99 | 2.76 – j1.68 | 22.6 | 49.0 | 80 | 67.7 | –17 |
| 2025 | 4.03 – j6.34 | 5.09 + j6.21 | 1.91 – j1.94 | 22.2 | 50.1 | 102 | 65.0 | –18 |

| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | Max Drain Efficiency | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P3dB | | | | | |
| | | | $Z_{load}$ (2) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 0.90 – j3.49 | 1.20 + j3.90 | 3.07 – j1.83 | 21.0 | 49.9 | 97 | 71.4 | –25 |
| 1960 | 2.03 – j4.74 | 2.55 + j5.10 | 2.76 – j1.68 | 20.6 | 49.9 | 99 | 69.9 | –24 |
| 2025 | 4.03 – j6.34 | 6.23 + j6.35 | 2.04 – j1.25 | 21.2 | 49.5 | 89 | 67.6 | –27 |

(1) Load impedance for optimum P1dB efficiency.
(2) Load impedance for optimum P3dB efficiency.
$Z_{source}$ = Measured impedance presented to the input of the device at the package reference plane.
$Z_{in}$ = Impedance as measured from gate contact to ground.
$Z_{load}$ = Measured impedance presented to the output of the device at the package reference plane.

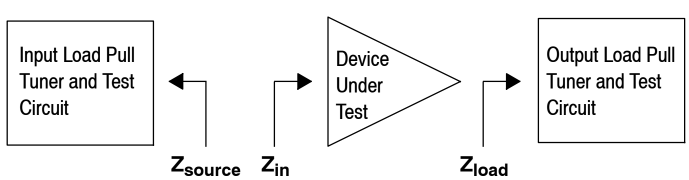


**Table 10. Peaking Side Load Pull Performance — Maximum Power Tuning**

$V_{DD}$ = 28 Vdc, $V_{GSB}$ = 1.7 Vdc, Pulsed CW, 10 μsec(on), 10% Duty Cycle

| | | | Max Output Power | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P1dB | | | | | |
| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | $Z_{load}$ (1) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 1.16 – j3.95 | 0.87 + j4.11 | 1.55 – j2.98 | 14.7 | 53.4 | 217 | 55.2 | –32 |
| 1960 | 2.19 – j5.24 | 1.69 + j5.51 | 1.64 – j2.91 | 14.7 | 53.5 | 223 | 57.5 | –31 |
| 2025 | 4.51 – j6.98 | 3.76 + j7.58 | 1.58 – j2.84 | 14.7 | 53.4 | 221 | 56.2 | –32 |

| | | | Max Output Power | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P3dB | | | | | |
| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | $Z_{load}$ (2) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 1.16 – j3.95 | 0.87 + j4.26 | 1.61 – j3.06 | 12.7 | 54.1 | 258 | 57.9 | –38 |
| 1960 | 2.19 – j5.24 | 1.80 + j5.80 | 1.67 – j3.08 | 12.6 | 54.2 | 263 | 58.5 | –38 |
| 2025 | 4.51 – j6.98 | 4.29 + j8.08 | 1.66 – j3.03 | 12.6 | 54.1 | 258 | 57.1 | –39 |

(1) Load impedance for optimum P1dB power.
(2) Load impedance for optimum P3dB power.
$Z_{source}$ = Measured impedance presented to the input of the device at the package reference plane.
$Z_{in}$ = Impedance as measured from gate contact to ground.
$Z_{load}$ = Measured impedance presented to the output of the device at the package reference plane.

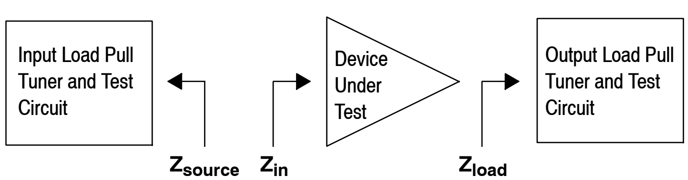
**Table 11. Peaking Side Load Pull Performance — Maximum Efficiency Tuning**

$V_{DD}$ = 28 Vdc, $V_{GSB}$ = 1.7 Vdc, Pulsed CW, 10 μsec(on), 10% Duty Cycle

| | | | Max Drain Efficiency | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P1dB | | | | | |
| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | $Z_{load}$ (1) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 1.16 – j3.95 | 0.81 + j4.10 | 3.98 – j2.80 | 15.5 | 51.9 | 154 | 66.6 | –37 |
| 1960 | 2.19 – j5.24 | 1.52 + j5.46 | 3.44 – j1.48 | 15.5 | 51.8 | 150 | 67.4 | –37 |
| 2025 | 4.51 – j6.98 | 3.36 + j7.55 | 2.72 – j1.22 | 15.5 | 51.8 | 150 | 66.5 | –38 |

| | | | Max Drain Efficiency | | | | | |
|---|---|---|---|---|---|---|---|---|
| | | | P3dB | | | | | |
| f (MHz) | $Z_{source}$ (Ω) | $Z_{in}$ (Ω) | $Z_{load}$ (2) (Ω) | Gain (dB) | (dBm) | (W) | $\eta_D$ (%) | AM/PM (°) |
| 1880 | 1.16 – j3.95 | 0.84 + j4.26 | 3.68 – j3.07 | 13.5 | 52.7 | 186 | 66.1 | –44 |
| 1960 | 2.19 – j5.24 | 1.69 + j5.79 | 3.33 – j2.09 | 13.4 | 52.8 | 191 | 66.7 | –44 |
| 2025 | 4.51 – j6.98 | 4.01 + j8.11 | 2.83 – j1.67 | 13.5 | 52.7 | 188 | 65.9 | –46 |

(1) Load impedance for optimum P1dB efficiency.
(2) Load impedance for optimum P3dB efficiency.
$Z_{source}$ = Measured impedance presented to the input of the device at the package reference plane.
$Z_{in}$ = Impedance as measured from gate contact to ground.
$Z_{load}$ = Measured impedance presented to the output of the device at the package reference plane.



## P1dB – TYPICAL CARRIER SIDE LOAD PULL CONTOURS — 1960 MHz

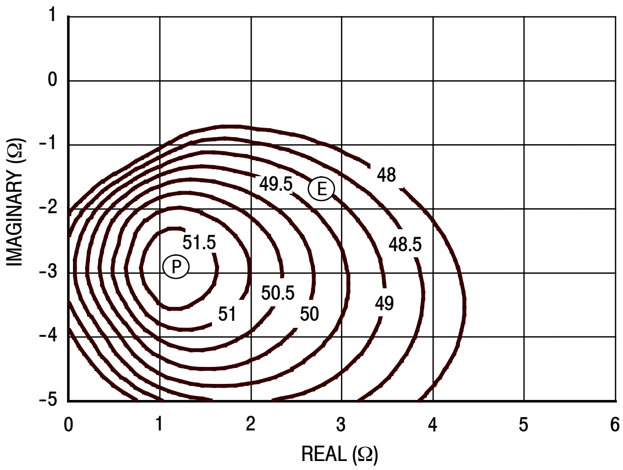



**Figure 8. P1dB Load Pull Output Power Contours (dBm)**

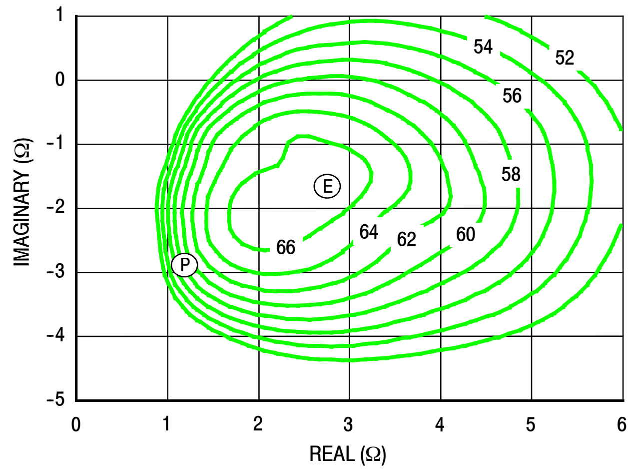



**Figure 9. P1dB Load Pull Efficiency Contours (%)**

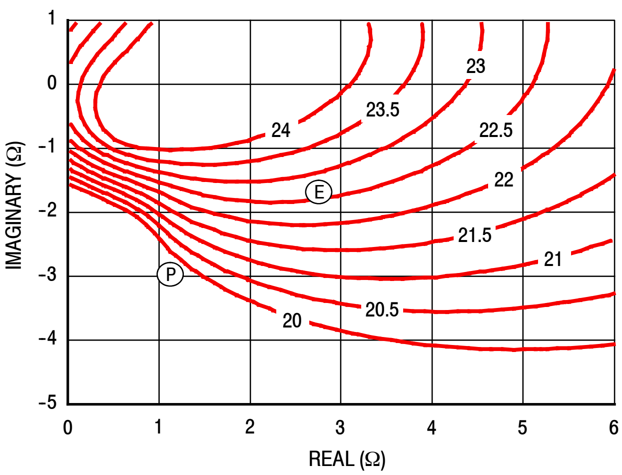



**Figure 10. P1dB Load Pull Gain Contours (dB)**

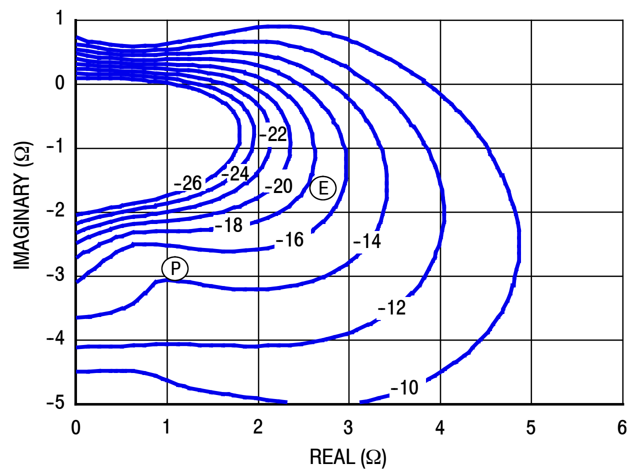



**Figure 11. P1dB Load Pull AM/PM Contours (°)**

**NOTE:** (P) = Maximum Output Power

(E) = Maximum Drain Efficiency

Gain

Drain Efficiency

Linearity

Output Power

## P3dB – TYPICAL CARRIER SIDE LOAD PULL CONTOURS — 1960 MHz

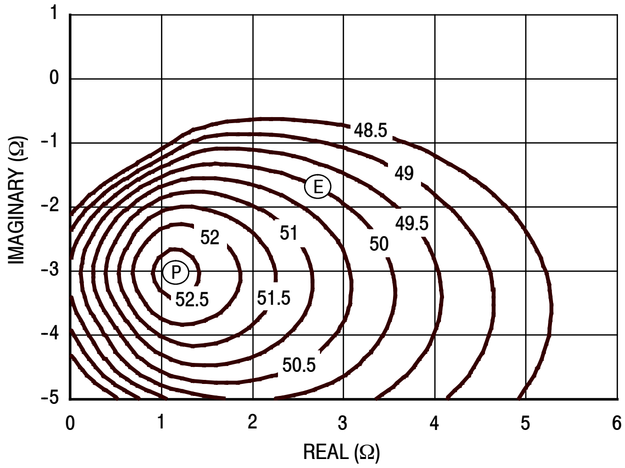



Figure 12. P3dB Load Pull Output Power Contours (dBm)

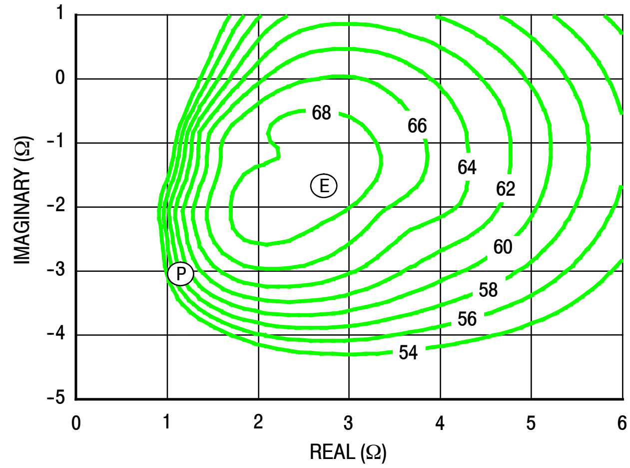



Figure 13. P3dB Load Pull Efficiency Contours (%)

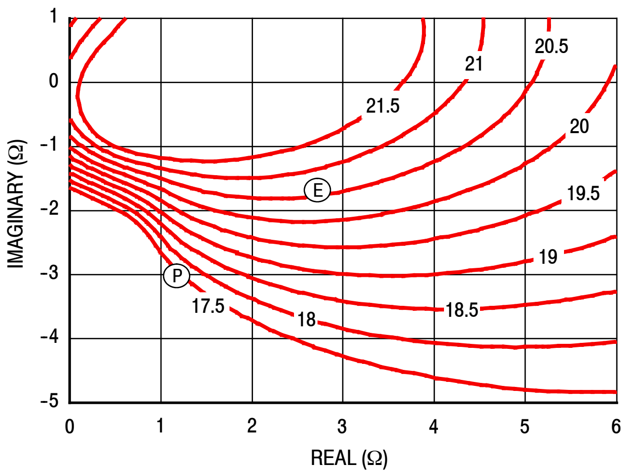



Figure 14. P3dB Load Pull Gain Contours (dB)

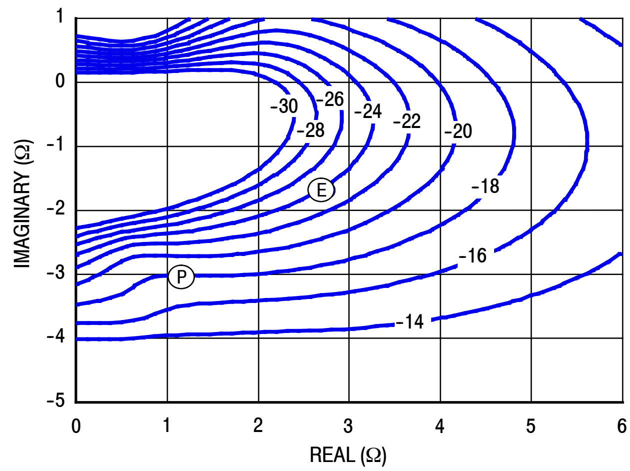



Figure 15. P3dB Load Pull AM/PM Contours (°)

**NOTE:** Ⓟ = Maximum Output Power
Ⓔ = Maximum Drain Efficiency

Gain
Drain Efficiency
Linearity
Output Power

## P1dB – TYPICAL PEAKING SIDE LOAD PULL CONTOURS — 1960 MHz

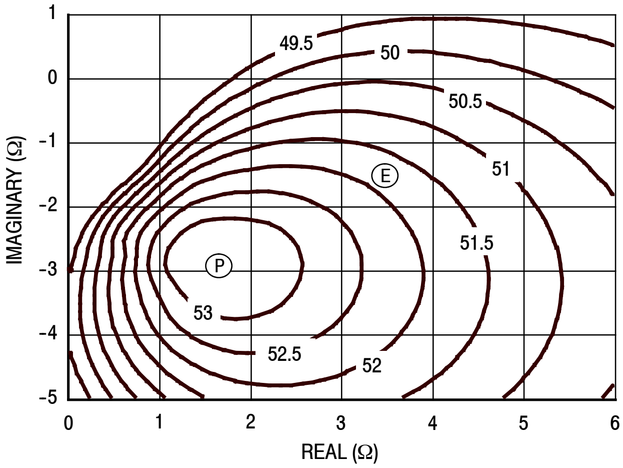



**Figure 16. P1dB Load Pull Output Power Contours (dBm)**

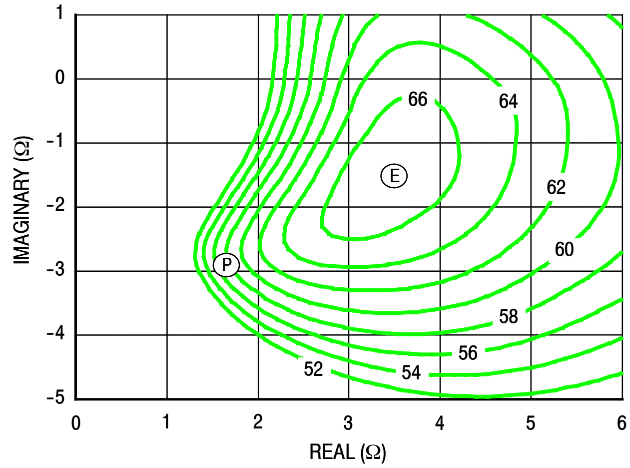



**Figure 17. P1dB Load Pull Efficiency Contours (%)**

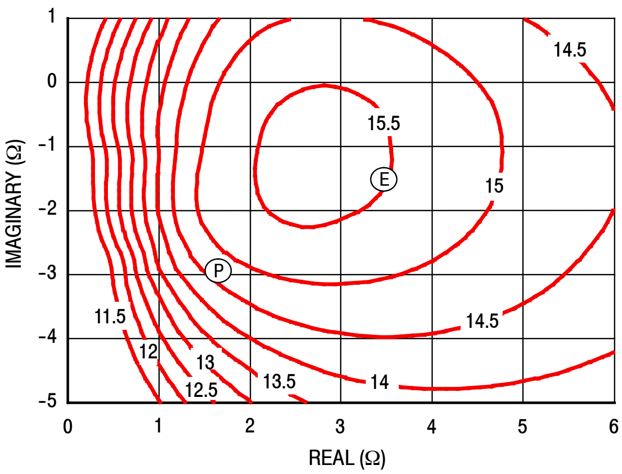



**Figure 18. P1dB Load Pull Gain Contours (dB)**

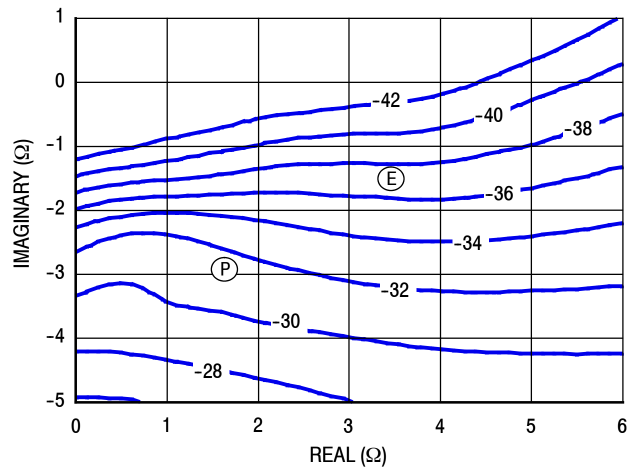



**Figure 19. P1dB Load Pull AM/PM Contours (°)**

**NOTE:** Ⓟ = Maximum Output Power

Ⓔ = Maximum Drain Efficiency

Gain

Drain Efficiency

Linearity

Output Power

## P3dB - TYPICAL PEAKING SIDE LOAD PULL CONTOURS — 1960 MHz

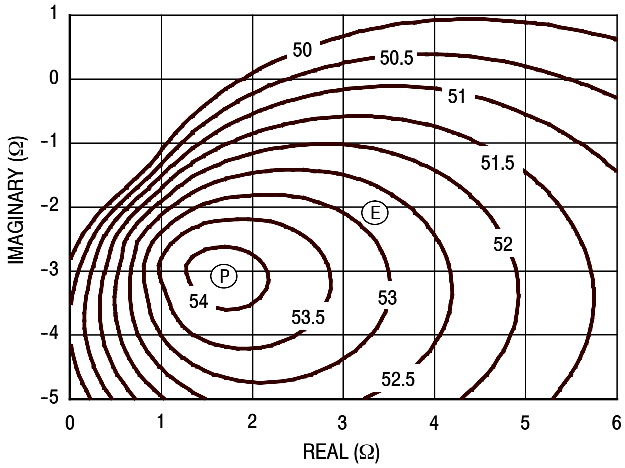



**Figure 20. P3dB Load Pull Output Power Contours (dBm)**

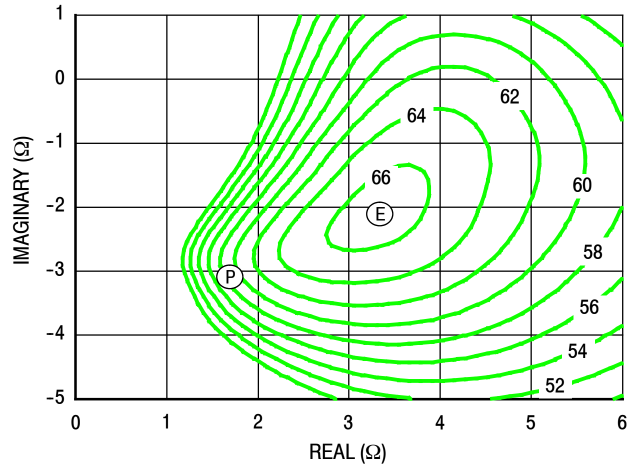



**Figure 21. P3dB Load Pull Efficiency Contours (%)**

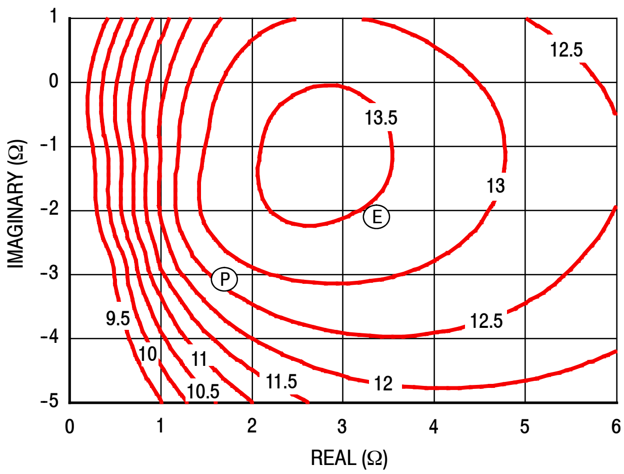



**Figure 22. P3dB Load Pull Gain Contours (dB)**

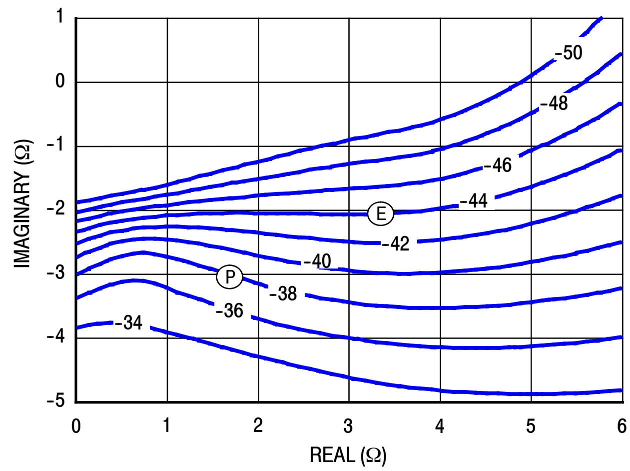
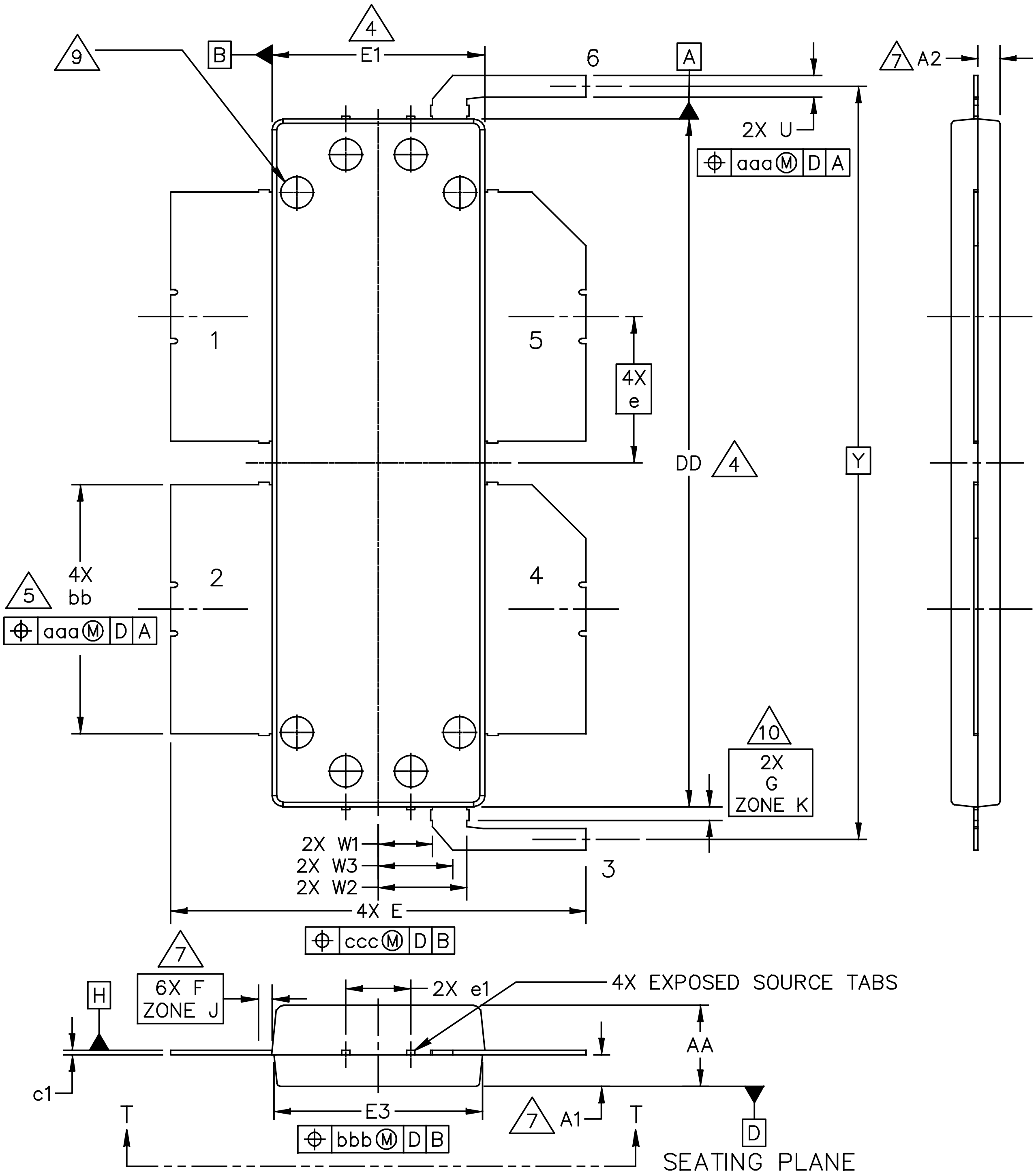



**Figure 23. P3dB Load Pull AM/PM Contours (°)**

**NOTE:** Ⓟ = Maximum Output Power

Ⓔ = Maximum Drain Efficiency

- Gain
- Drain Efficiency
- Linearity
- Output Power

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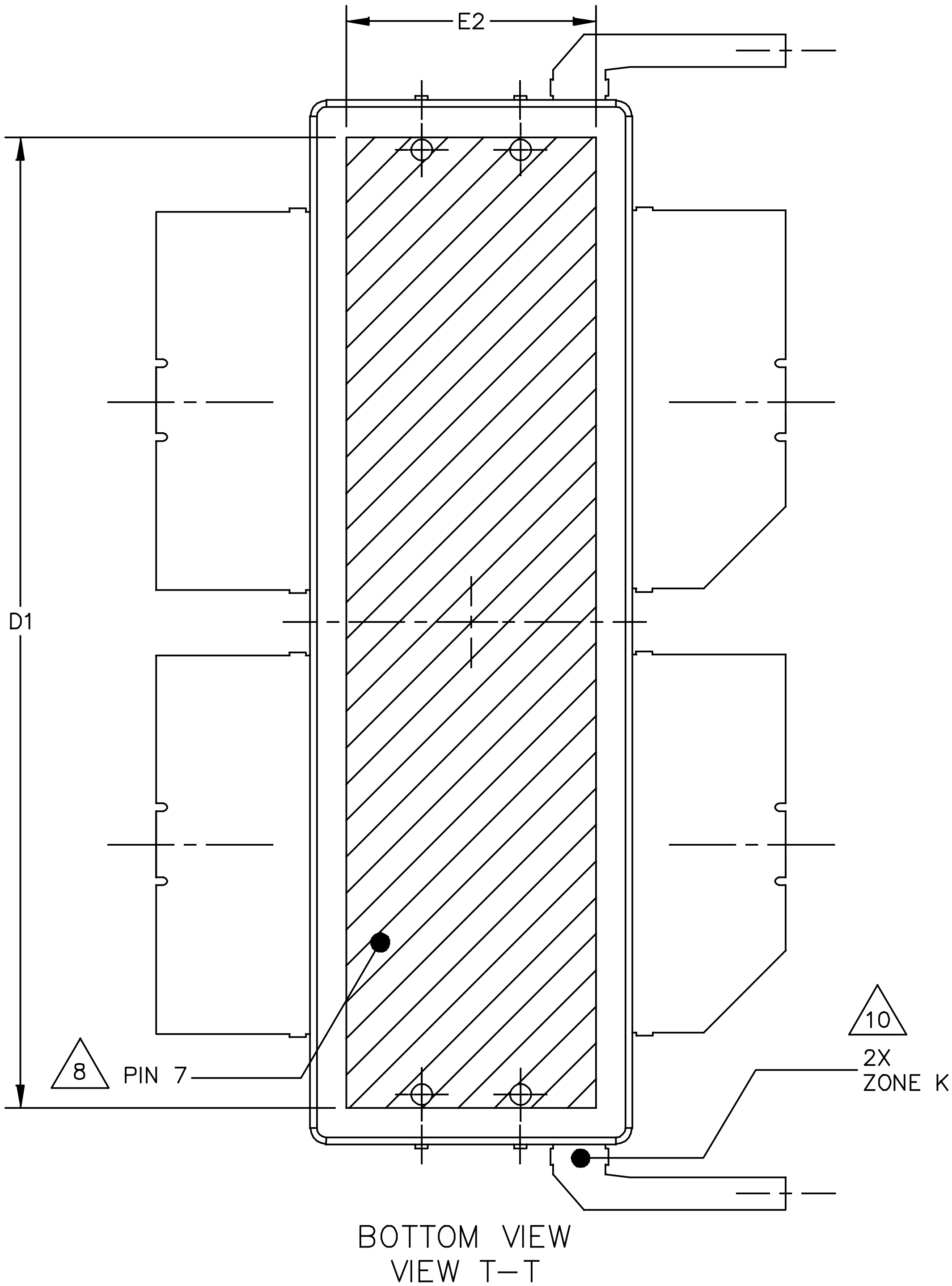


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| | SOT1819–1 17 FEB 2016 | |

NOTES:

1. CONTROLLING DIMENSION: INCH

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.

3. DATUM PLANE H IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.

4. DIMENSIONS DD AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 INCH (0.15 MM) PER SIDE. DIMENSIONS DD AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.

5. DIMENSION bb DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 INCH (0.13 MM) TOTAL IN EXCESS OF THE bb DIMENSION AT MAXIMUM MATERIAL CONDITION.

6. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.

7. DIMENSIONS A1 AND A2 APPLY WITHIN ZONE J ONLY. A1 APPLIES TO PINS 1, 2, 4 AND 5. A2 APPLIES TO PINS 3 AND 6.

8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. THE DIMENSIONS D1 AND E2 REPRESENT THE VALUES BETWEEN THE TWO OPPOSITE POINTS ALONG THE EDGES OF EXPOSED AREA OF HEAT SLUG.

9. DIMPLED HOLE REPRESENTS INPUT SIDE.

10. ZONE K REPRESENTS NON–SOLDERABLE REGION WHERE MOLD FLASH AND RESIN BLEED ARE PERMITTED ON BOTH SIDES OF THE LEADS.

| | INCH | | MILLIMETER | | | INCH | | MILLIMETER | |
|---|---|---|---|---|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX | DIM | MIN | MAX | MIN | MAX |
| AA | 0.148 | .152 | 3.76 | 3.86 | W1 | .095 | .105 | 2.41 | 2.67 |
| A1 | .059 | .065 | 1.50 | 1.65 | W2 | .158 | .168 | 4.01 | 4.27 |
| A2 | .056 | .068 | 1.42 | 1.73 | W3 | .132 | .142 | 3.35 | 3.61 |
| DD | 1.267 | 1.273 | 32.18 | 32.33 | U | .037 | .043 | 0.94 | 1.09 |
| D1 | 1.180 | ---- | 29.97 | ---- | Y | 1.390 BSC | | 35.31 BSC | |
| E | .762 | .770 | 19.35 | 19.56 | bb | .457 | .463 | 11.61 | 11.76 |
| E1 | .390 | .394 | 9.91 | 10.01 | c1 | .007 | .011 | 0.18 | 0.28 |
| E2 | .306 | ---- | 7.77 | ---- | e | .270 BSC | | 6.86 BSC | |
| E3 | .383 | .387 | 9.73 | 9.83 | e1 | .116 | .124 | 2.95 | 3.15 |
| F | .025 BSC | | 0.64 BSC | | aaa | .004 | | 0.10 | |
| G | .030 BSC | | 0.76 BSC | | bbb | .006 | | 0.15 | |
| | | | | | ccc | .010 | | 0.25 | |



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## PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following resources to aid your design process.

**Application Notes**

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Over-Molded Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

**Engineering Bulletins**

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

**Software**

- Electromigration MTTF Calculator
- .s2p File

**Development Tools**

- Printed Circuit Boards

**To Download Resources Specific to a Given Part Number:**

1. Go to http://www.nxp.com/RF
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

## REVISION HISTORY

The following table summarizes revisions to this document.

| Revision | Date | Description |
|---|---|---|
| 0 | Sept. 2016 | • Initial release of data sheet |

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Document Number: A2T20H330W24N
Rev. 0, 9/2016